

P-Channel 60 V (D-S) MOSFET

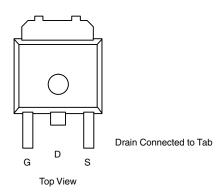
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ)		
- 60	0.155 at V _{GS} = - 10 V	- 8.4	12.5		
- 60	0.280 at V _{GS} = - 4.5 V	- 7.4	12.5		

FEATURES

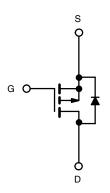
- TrenchFET® Power MOSFETS
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912







Ordering Information: SUD08P06-155L-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I.	- 8.2			
Continuous Diam Guitent (1) = 130 C)	T _C = 100 °C	I _D	- 5.2			
Pulsed Drain Current	I _{DM}	- 18	Α			
Continuing Source Current (Diode Conduction)	I _S	- 8.4				
Avalanche Current	I _{AS}	- 12	1			
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	7.2	mJ		
Maximum Daylar Dissination	T _C = 25 °C	P _D	20.8 ^a	W		
Maximum Power Dissipation	T _A = 25 °C	r D	1.7 ^b			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lumation to Ambiomth	t ≤ 10 s	R_{thJA}	20	25	°C/W	
Junction-to-Ambient ^b	Steady State		62	75		
Junction-to-Case		R _{thJC}	5	6		

Notes:

- a. See SOA curve for voltage derating.
- b. Surface mounted on 1" x 1" FR-4 boad.

SUD08P06-155L-GE3

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	- 2	- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50		
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 150		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 10			Α	
		V _{GS} = - 10 V, I _D = - 5 A		0.125	0.155		
D : 0	D	V _{GS} = - 10 V, I _D = - 5 A, T _J = 125 °C			0.280		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A, T _J = 150 °C			0.350	Ω	
		V _{GS} = - 4.5 V, I _D = - 2 A		0.158	0.280		
Forward Transconductance ^b	9 _{fs}	V _{DS} = - 15 V, I _D = - 5 A		8		S	
Dynamic	*						
Input Capacitance	C _{iss}			450		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		65			
Reverse Transfer Capacitance	C _{rss}			40			
Total Gate Charge	Qg			12.5	19		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8.4 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			3.2			
Gate Resistance	R_g	f = 1 MHz		8		Ω	
Turn-On Delay Time ^c	t _{d(on)}			5	10		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_{L} = 3.57 \Omega$		14	25	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 8.4 A, V_{GEN} = - 10 V, R_G = 2.5 Ω		15	25	ns	
Fall Time ^c	t _f]		7	12]	
Source-Drain Diode Ratings and Characteristics $(T_C = 25 ^{\circ}C)^b$							
Pulsed Current	I _{SM}				- 20	Α	
Forward Voltage ^b	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		- 0.9	- 1.3	V	
Reverse Recovery Time	t _{rr}	I _E = - 8 A, dI/dt = 100 A/μs		50	80	ns	
Reverse Recovery Time	Q _{rr}	- i _F = - δ A, αί/αι = 100 A/μS		80	120	nC	

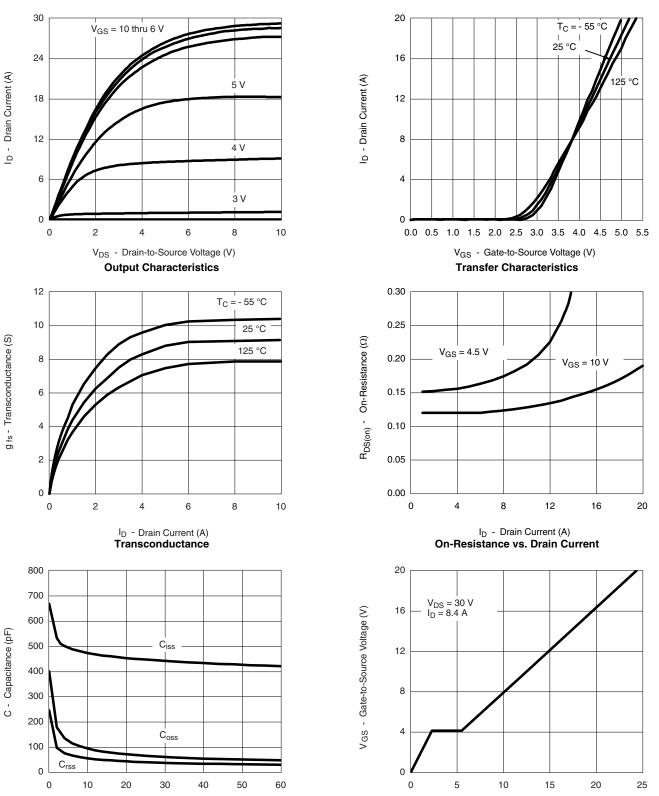
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)



V_{DS} - Drain-to-Source Voltage (V)

Capacitance

Q_q - Total Gate Charge (nC)

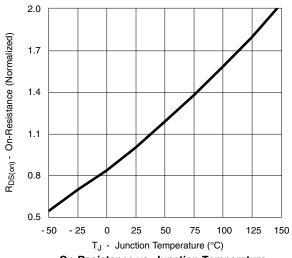
Gate Charge

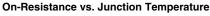
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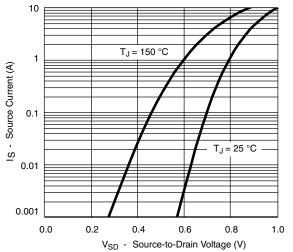
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TYPICAL CHARACTERISTICS (25 °C unless noted)



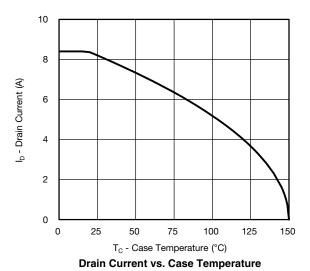






Source-Drain Diode Forward Voltage

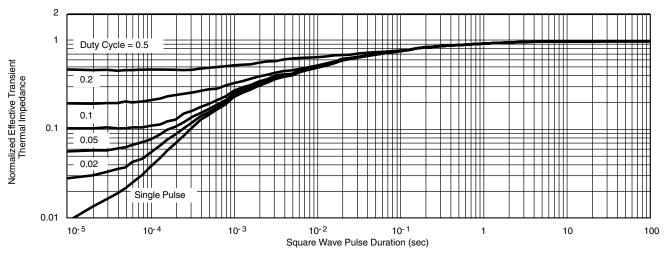
THERMAL RATINGS



100 10 100 µs I_D - Drain Current (A) 1 ms 10 ms DC, 10 s, 1 s, 100 ms 0.01 $T_C = 25 \, ^{\circ}C$ **BVDSS Limited** Single Pulse 0.001 0.1 10 100 $\rm V_{DS}$ - Drain-to-Source Voltage (V) * V $_{GS}$ > minimum V $_{GS}$ at which $\rm R_{DS(on)}$ is specified Safe Operating Area

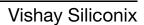
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THERMAL RATINGS



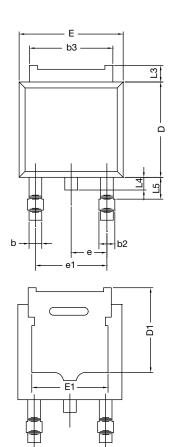
Normalized Thermal Transient Impedance, Junction-to-Case

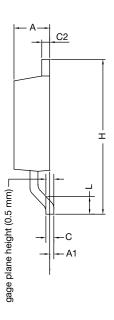
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishav.com/ppg262843.





TO-252AA Case Outline



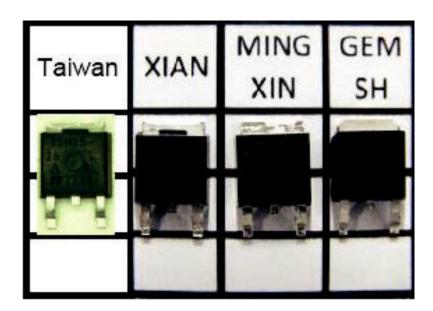


	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13					

DWG: 5347

Notes

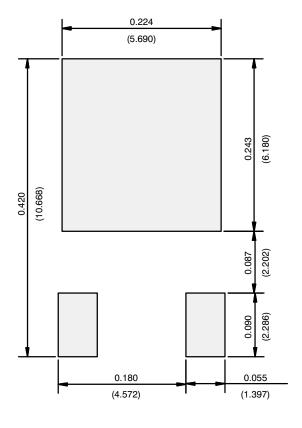
- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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